

CLAIMS

1. A thick film photoresist composition comprising:

(A) a resin component containing (a) from 61 to 90% by weight of a structural unit derived from a cyclic alkyl (meth)acrylate ester, and (b) a structural unit derived from a radical polymerizable compound containing a hydroxyl group,

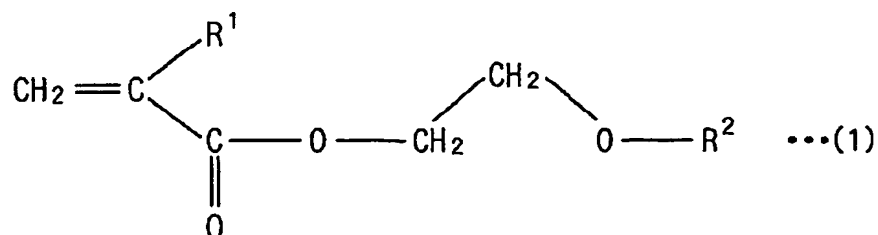
(B) a polymerizable compound containing at least one ethylenic unsaturated double bond,

(C) a photopolymerization initiator, and

(D) an organic solvent.

2. A thick film photoresist composition according to claim 1, wherein said structural unit (b) accounts for at least 1% by weight, but less than 10% by weight, of said component (A).

3. A thick film photoresist composition according to claim 1, wherein said component (A) further comprises (c) a structural unit derived from a radical polymerizable compound represented by a general formula (1) shown below:



(wherein, R¹ represents a hydrogen atom or a methyl group, and R² represents a hydrogen atom or an alkyl group of 1 to 4 carbon atoms).

4. A thick film photoresist composition according to claim 1, wherein said

5 component (D) is at least one solvent selected from a group consisting of methyl isobutyl ketone and methyl ethyl ketone.

5. A method of forming a resist pattern, wherein said resist pattern is formed using a thick film photoresist composition according to any one of claim 1 through claim 4.

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6. A pattern formed using said method disclosed in claim 5.